



《风光欣》技术资料

2SD882

NPN EPITAXIAL SILICON TRANSISTOR

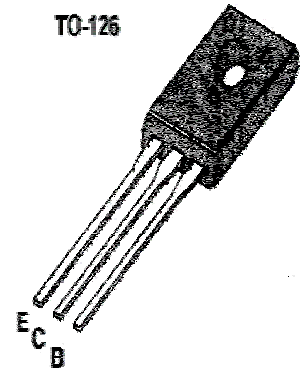
AUDIO FREQUENCY POWER AMPLIFIER

LOW SPEED SWITCHING

*Complement to 2SB772

ABSOLUTE MAXIMUM RATINGS(Ta=25)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	40	V
Collector-Emitter Voltage	V _{CEO}	30	V
Emitter -Base Voltage	V _{EBO}	5	V
Collector Current (DC)	I _c	3	A
Collector Current (Pulse)	I _c	7	A
Base Current (DC)	I _B	0.6	A
Collector Dissipation (Tc=25)	P _c	10	W
Collector Dissipation (Ta=25)	P _c	1	W
Junction Temperature	T _J	150	
Storage Temperature	T _{STG}	-55 ~150	



ELECTRICAL CHARACTERISTICS(Ta=25)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Cutoff Current	I _{CB0}	V _{CB} = 30V,I _E =0			1	μ A
Emitter-Cutoff Current	I _{EBO}	V _{EB} = 3V,I _c =0			1	μ A
*DC Current Gain	h _{FE1}	V _{CE} = 2V,I _c = 20mA	30	150		
	h _{FE2}	V _{CE} = 2V,I _c = 1A	60	160	400	
*Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _c = 2A,I _B = 0.2A		0.3	0.5	V
Base-Emitter Saturation Voltage	V _{BE(sat)}	I _c = 2A,I _B = 0.2A		1.0	2.0	V
Current Gain-Bandwidth Product	f _T	V _{CE} = 5V,I _E =0.1A		90		MHZ
Output Capacitance	C _{OB}	V _{CB} = 10V,I _E =0,f=1MHZ		45.0		pF

*Pulse Test :PW <350uS, Duty Cycle <2%

HFE (2) CLASSIFICATION

Classification	R	Q	P	I
HFE(2)	60-120	100-200	160-320	200-400